



## BD244 – A – B – C

### SILICON PNP POWER TRANSISTORS

The BD244 series are PNP power transistors in a TO-220 envelope. They are intended for use in medium power linear and switching applications. The complementary is BD243, A, B, C  
Compliance to RoHS.

#### ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value	Unit	
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0mA$ )	BD244	-45	V
		BD244A	-60	
		BD244B	-80	
		BD244C	-100	
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0mA$ )	BD244	-45	V
		BD244A	-60	
		BD244B	-80	
		BD244C	-100	
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0mA$ )	-5.0	V	
$I_C$	Collector Current	-6	A	
$I_{CM}$	Collector Current-Peak	-10		
$I_B$	Base Current	-2	A	
$P_T$	Collector Power Dissipation	$T_C = 25^\circ C$ 65	W	
$T_J$	Junction Temperature	150	$^\circ C$	
$T_S$	Storage Temperature	-65 to +150		

#### THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
$R_{thJC}$	Junction to Case Thermal Resistance	1.92	$^\circ C / W$
$R_{thJA}$	Junction to free air Thermal Resistance	62.5	$^\circ C / W$



## BD244 – A – B – C

### ELECTRICAL CHARACTERISTICS

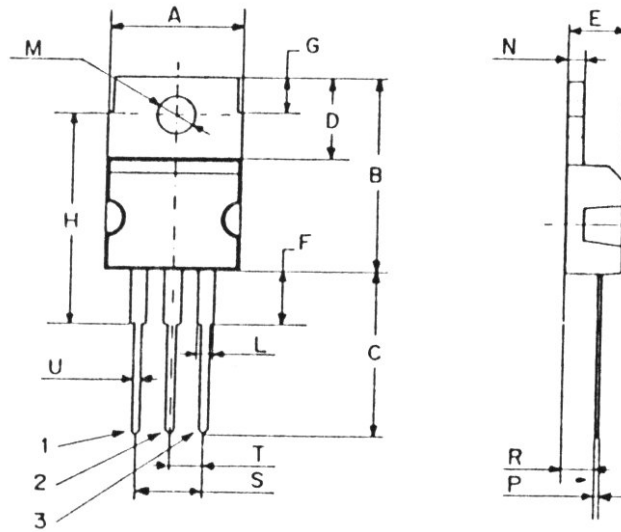
TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Max	Unit	
$I_{CES}$	Collector- Emitter Cut-off Current	$V_{CE} = -45\text{ V}, V_{BE} = 0$   BD244	-	-	-0.4	mA	
		$V_{CE} = -60\text{ V}, V_{BE} = 0$   BD244A					
		$V_{CE} = -80\text{ V}, V_{BE} = 0$   BD244B					
		$V_{CE} = -100\text{ V}, V_{BE} = 0$   BD244C					
$I_{CEO}$	Collector Cut-off Current	$V_{CE} = -30\text{ V}, I_B = 0$   BD244	-	-	-0.7	mA	
		$V_{CE} = -30\text{ V}, I_B = 0$   BD244A					
		$V_{CE} = -60\text{ V}, I_B = 0$   BD244B					
		$V_{CE} = -60\text{ V}, I_B = 0$   BD244C					
$I_{EBO}$	Emitter Cut-off Current	$V_{EB} = -5\text{ V}, I_C = 0$	-	-	-1	mA	
$V_{CEO}$	Collector- Emitter Breakdown Voltage (*)	$I_C = -30\text{ mA}, I_B = 0$	BD244	-45	-	-	V
			BD244A	-60	-	-	
			BD244B	-80	-	-	
			BD244C	-100	-	-	
$h_{FE}$	DC Current Gain (*)	$V_{CE} = -4\text{ V}, I_C = -0.3\text{ A}$	30	-	-	-	
		$V_{CE} = -4\text{ V}, I_C = -3\text{ A}$	15	-	-		
$V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$I_C = -6\text{ A}, I_B = -1\text{ A}$	-	-	-1	V	
$V_{BE}$	Base-Emitter Voltage(*)	$V_{CE} = -4\text{ V}, I_C = -6\text{ A}$	-	-	-1.6	V	

## BD244 – A – B – C

### MECHANICAL DATA CASE TO-220

DIMENSIONS (mm)		
	Min.	Max.
A	9,90	10,30
B	15,65	15,90
C	13,20	13,40
D	6,45	6,65
E	4,30	4,50
F	2,70	3,15
G	2,60	3,00
H	15,75	17,15
L	1,15	1,40
M	3,50	3,70
N	-	1,37
P	0,46	0,55
R	2,50	2,70
S	4,98	5,08
T	2,49	2,54
U	0,70	0,90



Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter
Package	Collector

Revised August 2012

Information furnished is believed to be accurate and reliable. However, Comset Semiconductors assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. Data are subject to change without notice. Comset Semiconductors makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Comset Semiconductors assume any liability arising out of the application or use of any product and specifically disclaims any and all liability, including without limitation consequential or incidental damages. Comset Semiconductors' products are not authorized for use as critical components in life support devices or systems.